

## Target:

Towards wafer-scale integration of air stable QDs on commercial silicon read-out integrated circuits.

## Challenges:

- Facile, localized QD film patterning
- Long life-time photostability

## Transfer Printing Approach:

Selective pick-and-print of  $\text{Al}_2\text{O}_3$  passivated QD assemblies on device structures with high precision.

## Scalability

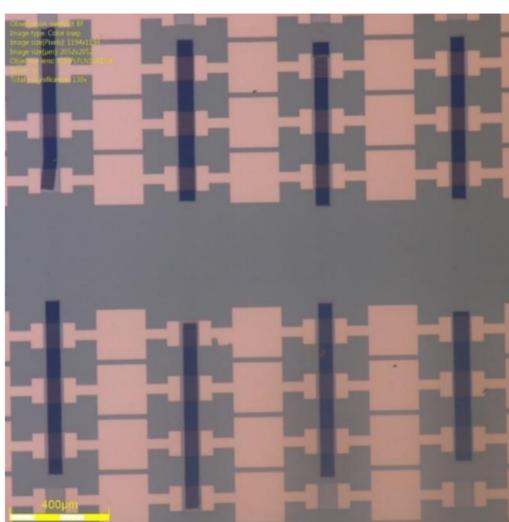


Fig.2 Integrated Arrays of printed  $\text{Al}_2\text{O}_3$ @ $\text{PbS}_{2.1\mu\text{m}}$  QD photoconductors

## Transfer Printing Process Flow

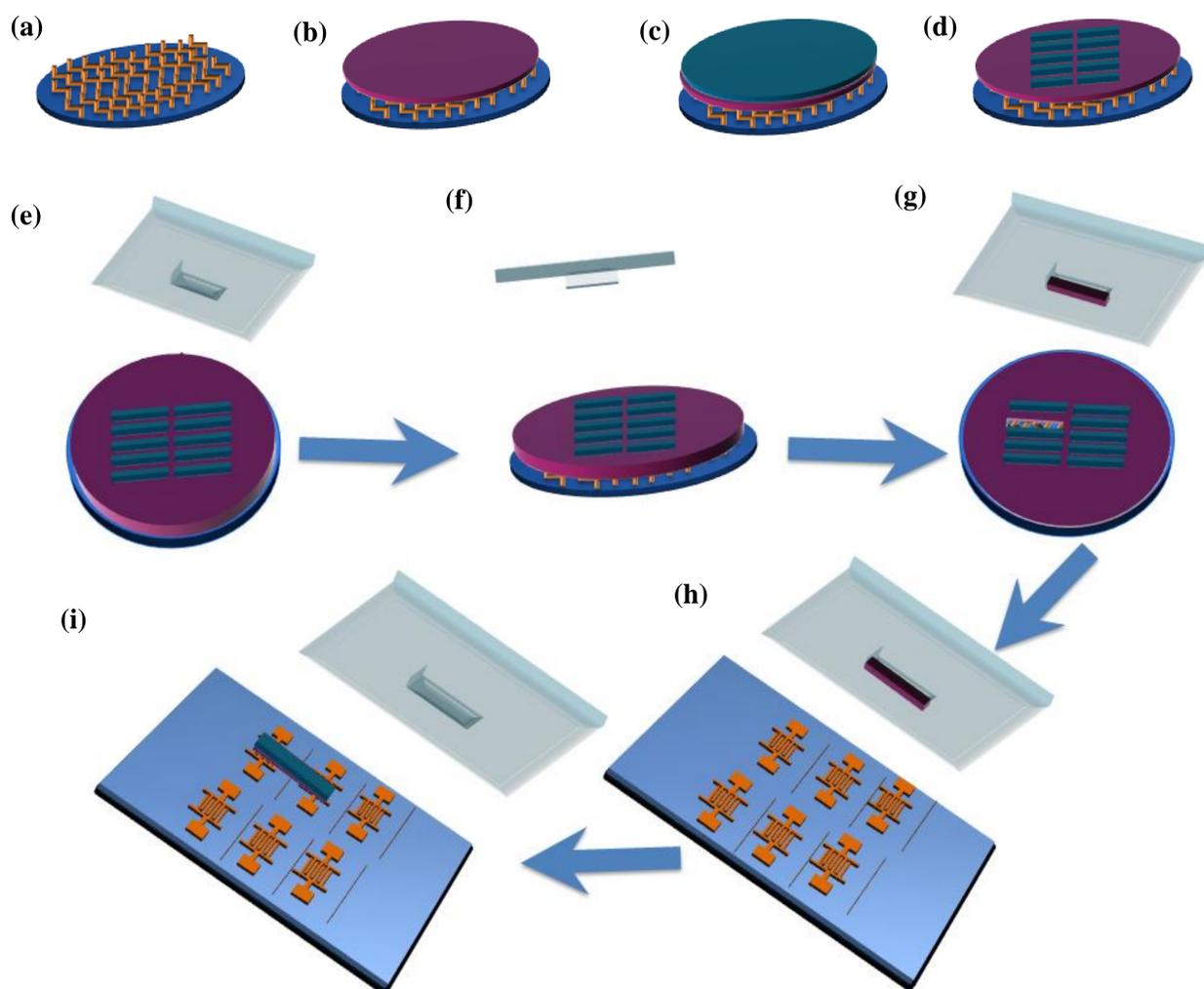


Fig.1 (a-d) **Source substrate preparation**, including ODTS-Si preparation, QDs spin coating and ALD- $\text{Al}_2\text{O}_3$  encapsulation. (e-i) **Pick-and-Print** of  $\text{Al}_2\text{O}_3$ /PbS patches on interdigitated electrodes on an oxidized Si wafer

## $\text{Al}_2\text{O}_3$ @ $\text{PbS}_{2.1\mu\text{m}}$ QD photoconductor characterization

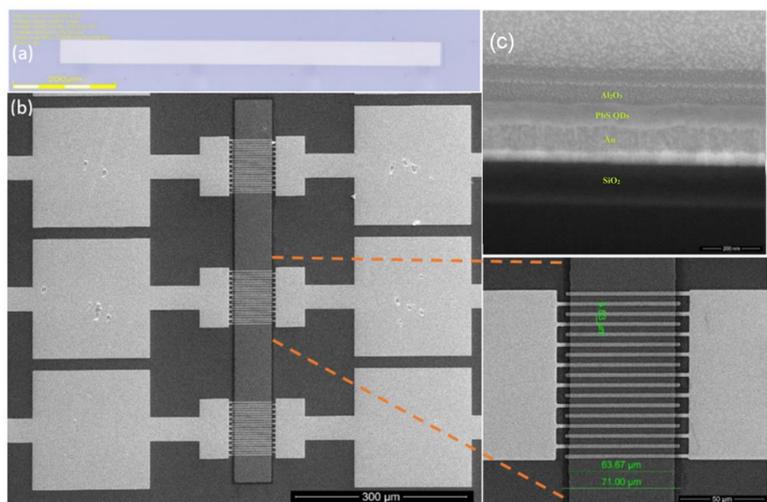


Fig.3 (a) optical image of the source substrate after pattern pick-up, (b) Printed  $\text{Al}_2\text{O}_3$ /PbS QD photoconductor, and (c) cross section.

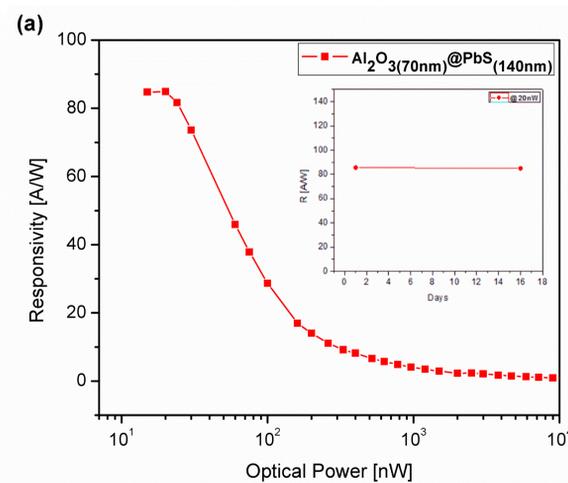
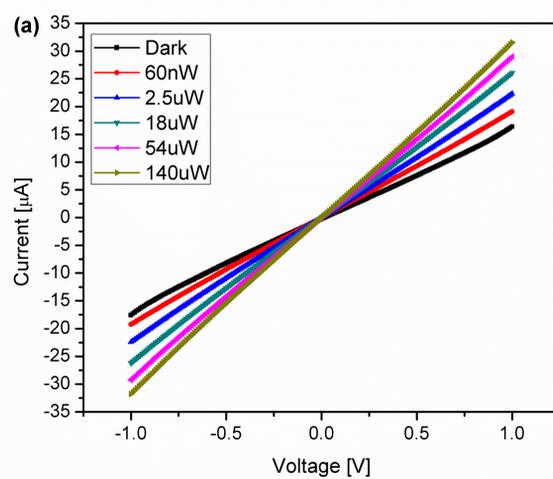


Fig.4 (a) IV characteristics in dark and under surface illumination at  $2.1\ \mu\text{m}$ , and (b) corresponding responsivity and (inset) life-time stability

